## P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)			
-60	0.012 at $V_{GS}$ = -10 V	-60			
	0.020 at $V_{GS}$ = -4.5 V	-50			

### FEATURES

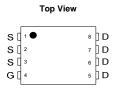
- FEATURES
- DT-Trench Power MOSFET
- + 100 %  $\rm R_g$  and UIS Tested

### APPLICATIONS

- Notebook
  - Load Switch

# DFN5X6 Top View Bottom View

PIN1



GO

S

D P-Channel MOSFET

PARAMETER		SYMBOL	Limit	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	- 60	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	v	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C		- 60		
	T <sub>A</sub> = 70 °C	I <sub>D</sub>	- 50		
Pulsed Drain Current		I <sub>DM</sub>	- 240	A	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 60		
Avalanche Current	e Current		- 62		
Single Pulse Avalanche Energy		E <sub>AS</sub>	225	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	р	43	W	
Maximum Fower Dissipation -	$T_A = 70 \ ^\circ C$	P <sub>D</sub>	38	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Soldering Recommendations (Peak Temperature) b, c			260		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	R <sub>thJA</sub>	15	23		
Maximum Junction-to-Amblent ~	Steady State		22	35	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	1	1.3		

### Notes

a. Surface mounted on 1" x 1" FR4 board.

b. TheDFN5x6isa lea<u>dlesspackage.The endof thel</u>ead terminalisexposedcopper (not plated) as a result of thesingulation process in manufacturing. A solderfillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequatebottom side solder interconnection.

c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

Din-Tek SEMICONDUCTOR



<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Static								
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \ \mu A$	-1	-	-3	V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V	-	-	± 100	nA		
	1	$V_{DS} = -48 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	-1			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = -48 V, $V_{GS}$ = 0 V, $T_J$ = 70 $^\circ C$	-	-	-10	μA		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \leq$ -5 V, $V_{GS}$ = -10 V	-60	-	-	А		
Drain-Source On-State Resistance <sup>a</sup>	Р	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -15 \text{ A}$	-	0.012	0.0145	Ω		
	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -10 \text{ A}$	-	0.020	0.0250			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -15 \text{ A}$	-	31	-	S		
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{\rm S}$ = -4.5 A, $V_{\rm GS}$ = 0 V	-	-0.7	-1.2	V		
Dynamic <sup>b</sup>								
Total Gate Charge	Qg		-	121	190			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = -30 V, $V_{GS}$ = -10 V, $I_{D}$ = -15 A	-	20	-	nC		
Gate-Drain Charge	Q <sub>gd</sub>		-	32	-			
Gate Resistance	Rg		-	3	-	Ω		
Turn-On Delay Time	t <sub>d(on)</sub>		-	20	30			
Rise Time	tr	$V_{DD}$ = -30 V, $R_L$ = 30 $\Omega$	-	20	30			
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ -15 A, $V_{GEN}$ = -10 V, $R_g$ = 6 $\Omega$	-	205	310	ns		
Fall Time	t <sub>f</sub>		-	90	135			
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = -4.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$	-	45	70			

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



55 °C

3.5

4.0

3.0

40

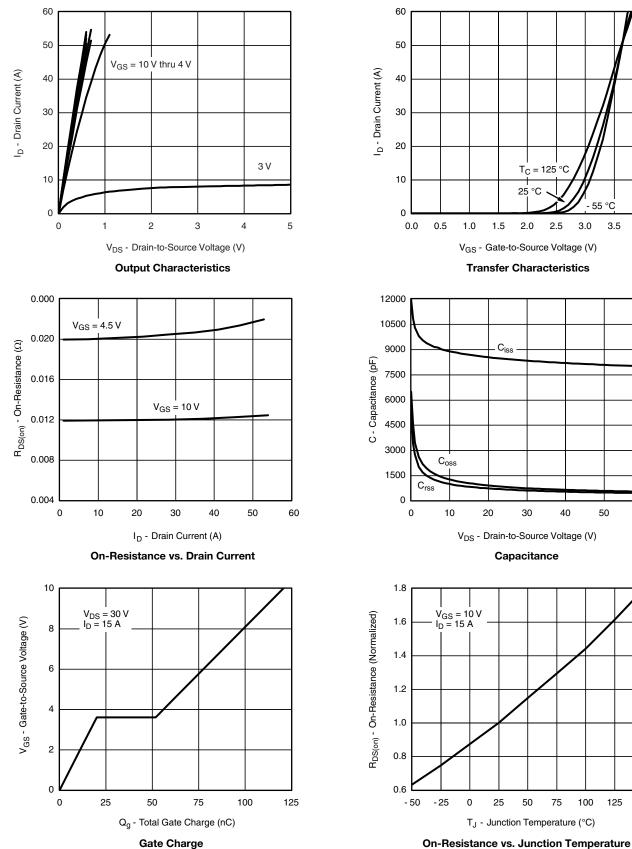
50

60

150

125

100



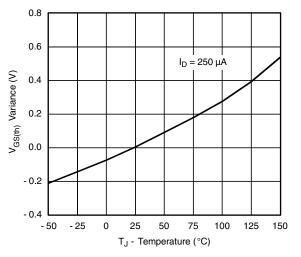
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



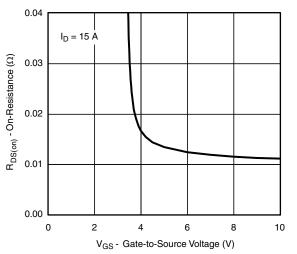
# $\begin{array}{c} 70 \\ (e) \\ (f) \\$



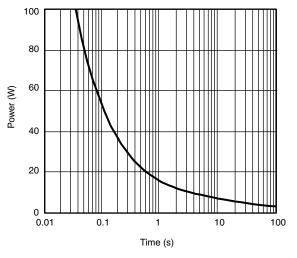




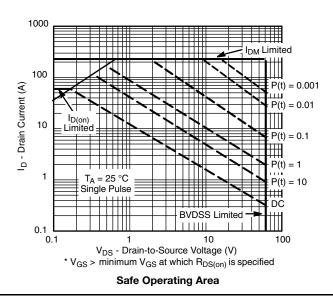




On-Resistance vs. Gate-to-Source Voltage



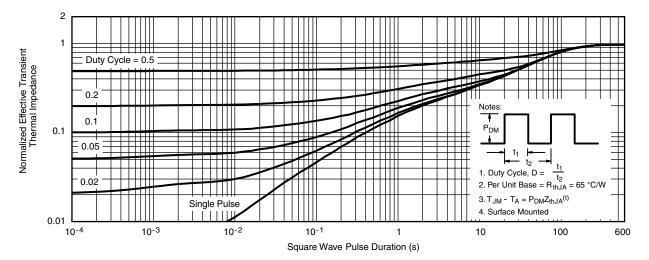
Single Pulse Power, Junction-to-Ambient

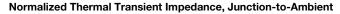


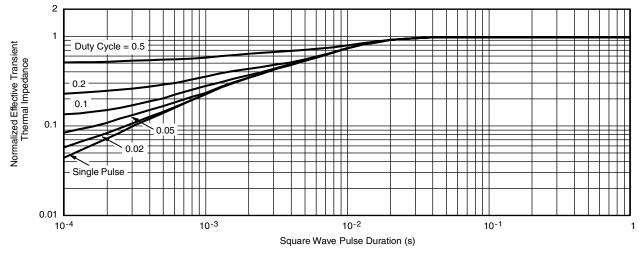
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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

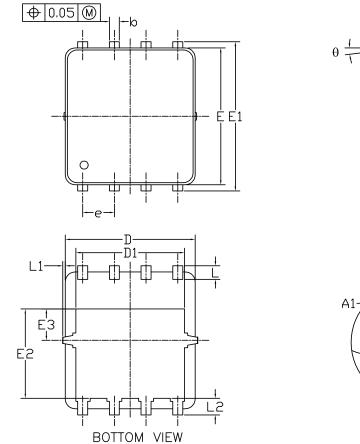




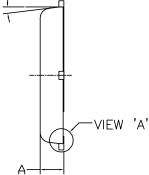


Normalized Thermal Transient Impedance, Junction-to-Case

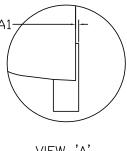
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<u>VIEW 'A'</u> (SCALE 5:1)

**RECOMMENDED LAND PATTERN** .60 -0.55 0.50 -0.77 -0.635 4.12 6.15 -1.60 +  $\left|+\right|$ + 0.65 +t -11.27-0.50-

and the late	DIMENS	IONS IN MILLI	METERS	DIMENSIONS IN INCHES			
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
А	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0.15	0.20	0.25	0.006	0.008	0.010	
D	4.80	5.20	5.30	0.201	0.205	0.209	
D1	4.25	4.35	4.45	0.167	0.171	0.175	
Е	5.45	5.55	5.65	0.215	0.219	0.222	
E1	5.95	6.05	6.15	0.234	0.238	0.242	
E2	3.525	3.625	3.725	0.139	0.143	0.147	
E3	1.175	1.275	1.375	0.046	0.050	0.054	
e	1.27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	

### UNIT: mm

NOTE 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH. 2. CONTROLLING DIMENSION IS MILLIMETER.

CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



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